

## EUROPEAN PATENT OFFICE

## Patent Abstracts of Japan

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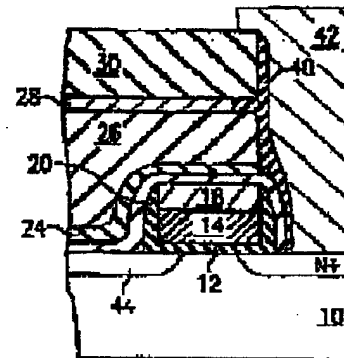
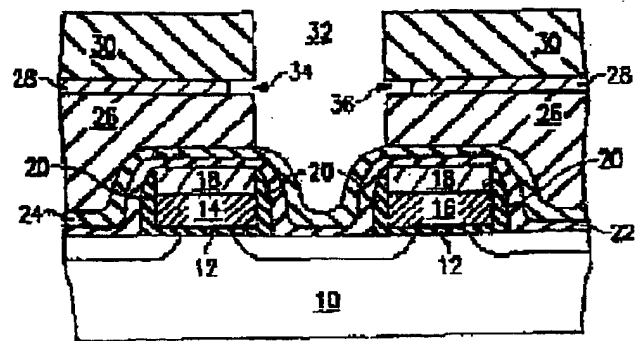
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APPLICANT : TEXAS INSTR INC <TI>;

INVENTOR : LIU JIANN;

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H01L 21/768

TITLE : SEMICONDUCTOR DEVICE AND ITS  
MANUFACTURE



ABSTRACT : PROBLEM TO BE SOLVED: To provide a semiconductor device and its manufacturing method with which the generation of a defective device and the loss of production can be reduced or removed.

SOLUTION: A contact hole 32 is formed penetrating a conductive layer 28. Then, the conductive layer 28 is undercut (34 and 36). An insulating layer 40 is formed in the contact hole 32. Then, a contact point 42 is formed in the contact hole 32.

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